RF071M2S

Diodes

Fast recovery diode **RF071M2S**

Applications

High frequency rectification

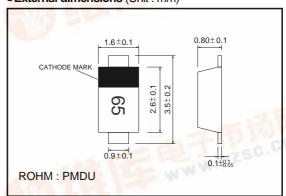
Features

- 1) Small power mold type (PMDS)
- 2) Ultra low V_F
- 3) Very fast recovery
- 4) Low switching loss

Construction

Silicon epitaxial planar

●External dimensions (Unit: mm)



● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V _{RM}	200	V
Reverse voltage (DC)	VR	200	V
Forward voltage (DC)	l _F *	1.0	Α
Average rectified forward current	lo *	0.7	А
Forward peak surge current (60Hz · 1cyc.)	IFSM	15	А
Junction temperature	J. 7, 15	150	°C
Storage temperature	Tstg	-55 to +150	°C

^{*} Mounting on glass epoxi board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	VF	-	0.790	0.850	V	I _F =0.7A
Reverse current	lR		10n	10μ	Α	V _R =200V
Reverse recovery time	trr	27- 17	ns	25	ns	IF=0.5A, IR=1.0A, Irr=0.25×IR
Note) ESD sensitive product handing i	required.	ozsc	COM			





●Electrical characteristic curves (Ta=25°C)

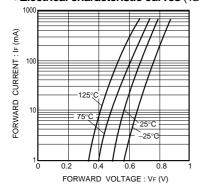


Fig.1 Forward temperature characteristics

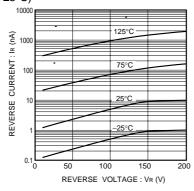


Fig.2 Reverse temperature characteristics

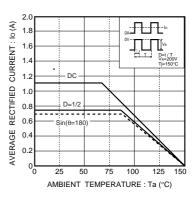


Fig.3 Derating curve

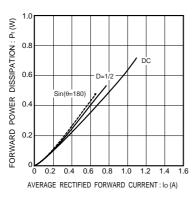


Fig. 4 Power dissipation characteristics

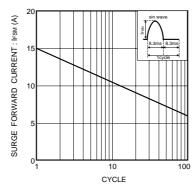


Fig.5 Forward peak surge current

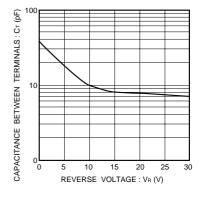


Fig. 6 Capacitance between terminals characteristics

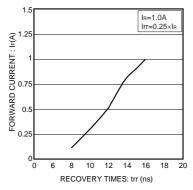


Fig. 7 Reverse recovery time

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